

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	9	(expos\$4 near10 pad near10 etch\$4) and gate and data and semiconductor and pixel and mask\$4 and ((mask cutting-off) near10 metal) and (((three "3") adj mask\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 12:54
S48	927	349/149	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:18
S49	963	349/187	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 15:29
S50	27	cutting-off adj plate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 15:37
S51	4883	expos\$4 near10 pad near10 etch\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 15:38
S52	237	(expos\$4 near10 pad near10 etch\$4) and gate and data and semiconductor and pixel and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 11:15

S54	24	(expos\$4 near10 pad near10 (dry adj etch\$4)) and gate and data and semiconductor and pixel and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 16:29
S55	94	(expos\$4 near10 pad near10 etch\$4) and gate and data and semiconductor and pixel and mask\$4 and cut\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 11:08
S56	2	(expos\$4 near10 pad near10 etch\$4) and gate and data and semiconductor and pixel and mask\$4 and cut\$4-off	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 11:08
S57	998	349/143	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:24
S58	367	349/150	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:24
S59	1653	349/43	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:25
S60	357	349/43 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:38
S61	73	349/150 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 11:50

S62	131	349/152 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:26
S63	114	349/143 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:37
S65	84	349/143 and pad and expos\$4 and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 11:48
S67	66	349/152 and pad and expos\$4 and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 11:37
S69	291	349/43 and pad and expos\$4 and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:39
S70	111	(expos\$4 near10 pad near10 etch\$4) and gate and data and semiconductor and pixel and mask\$4 and ((mask cutting-off) near10 metal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 12:53

